# P-Channel 200-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

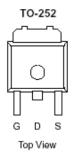
#### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	Id (A)		
-200	1400 @ V <sub>GS</sub> = -10V	-4.9		
	1600 @ V <sub>GS</sub> = -5.5V	-4.6		

in





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			-200	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	-4.9	А	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-20	~		
Continuous Source Current (Diode Conduction) <sup>a</sup>	ا <sub>s</sub>	-10	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	50	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\thetaJA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/ VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

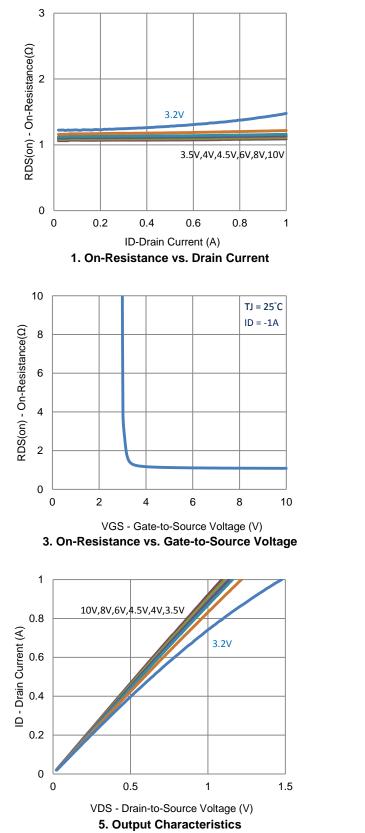
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -160 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			-1		
	DSS	$V_{DS} = -160 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	-7.5			А	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ A}$			1400	mΩ	
	r <sub>DS(on)</sub>	$V_{GS}$ = -5.5 V, I <sub>D</sub> = -0.8 A			1600		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -1 \text{ A}$		7		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.75		V	
	Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = -100 \text{ V}, \text{ V}_{GS} = -5.5 \text{ V},$ $I_{D} = -1 \text{ A}$		4		nC	
Gate-Source Charge	Q <sub>gs</sub>			1.0			
Gate-Drain Charge	$Q_{gd}$	1 <u>0</u> – 177		1.6			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = -100 V, R <sub>L</sub> = 100 Ω,		12			
Rise Time	t <sub>r</sub>	$V_{DS} = -100 V, K_{L} = 100 \Omega,$ $I_{D} = -1 A.$		8		ne	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		28		ns	
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = -10 \text{ v},  \text{R}_{\text{GEN}} = 0 \Omega$		16			
Input Capacitance	C <sub>iss</sub>			580			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = -15 V, $V_{GS}$ = 0 V, f = 1 Mhz		82		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			30			

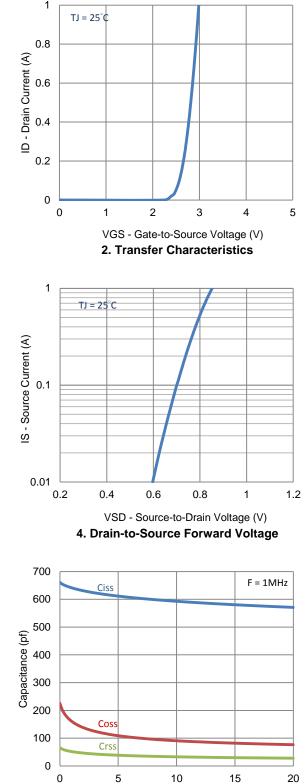
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

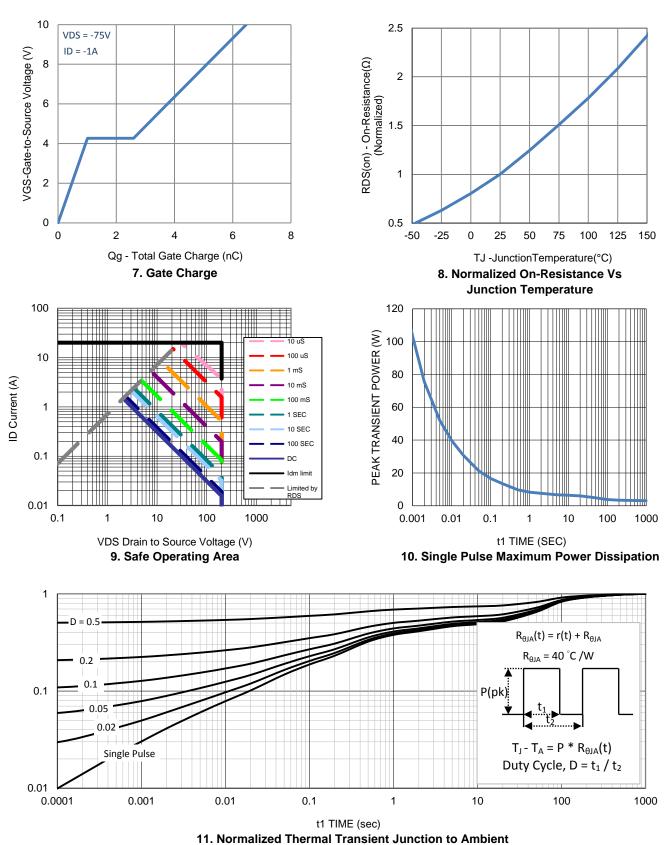
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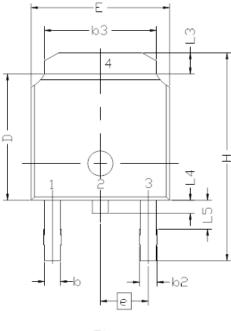


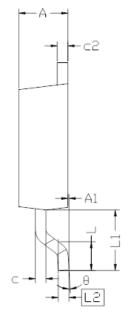
VDS-Drain-to-Source Voltage (V) 6. Capacitance

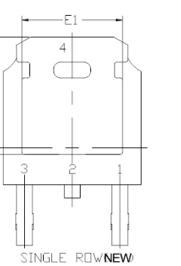


### **Typical Electrical Characteristics**

### **Package Information**







	DIMENSI	IONAL	REQMTS		
SYMBOL	MIN	NDM	MAX		
E	6.40	6.60	6.731		
L	1.40	1.52	1.77		
L1	2.743 REF				
L2	0.	508 BS			
L3	0.89		1.27		
L4	0.64		1.01		
L5					
D	6.00	6.10	6.223		
Н	9.40	10.00	10.40		
b	0.64	0.76	0,88		
b2	0.77	0.84	1.14		
b3	5.21	5.34	5.46		
e	2.	286 BS	SC		
A	2.20	2.30	2.38		
A1	0		0.127		
C	0.45	0.50	0.60		
c2	0.45	0.50	0.58		
D1	5.30				
E1	4.40				
θ	0°		10*		

Note:

1. All Dimension Are In mm.

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- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.